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RAPID COOLING OF CZ SILICON CRYSTAL GROWTH SYSTEM

Abstract of the Disclosure:

A Czochralski method for producing monocrystals wherein a single crystal silicon rod is pulled from a silicon melt contained in a crucible within a chamber. After pulling the single crystal silicon rod from a silicon melt in a chamber, the chamber is cooled by flowing a gas having a thermal conductivity of at least about 55×10^{-5} g.cal./(sec.$\bullet$cm^2)(°C/cm) at 800°K into the chamber. The preferred cooling gas is a helium-containing gas.

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